



N-M10

Monocrystalline Wafer

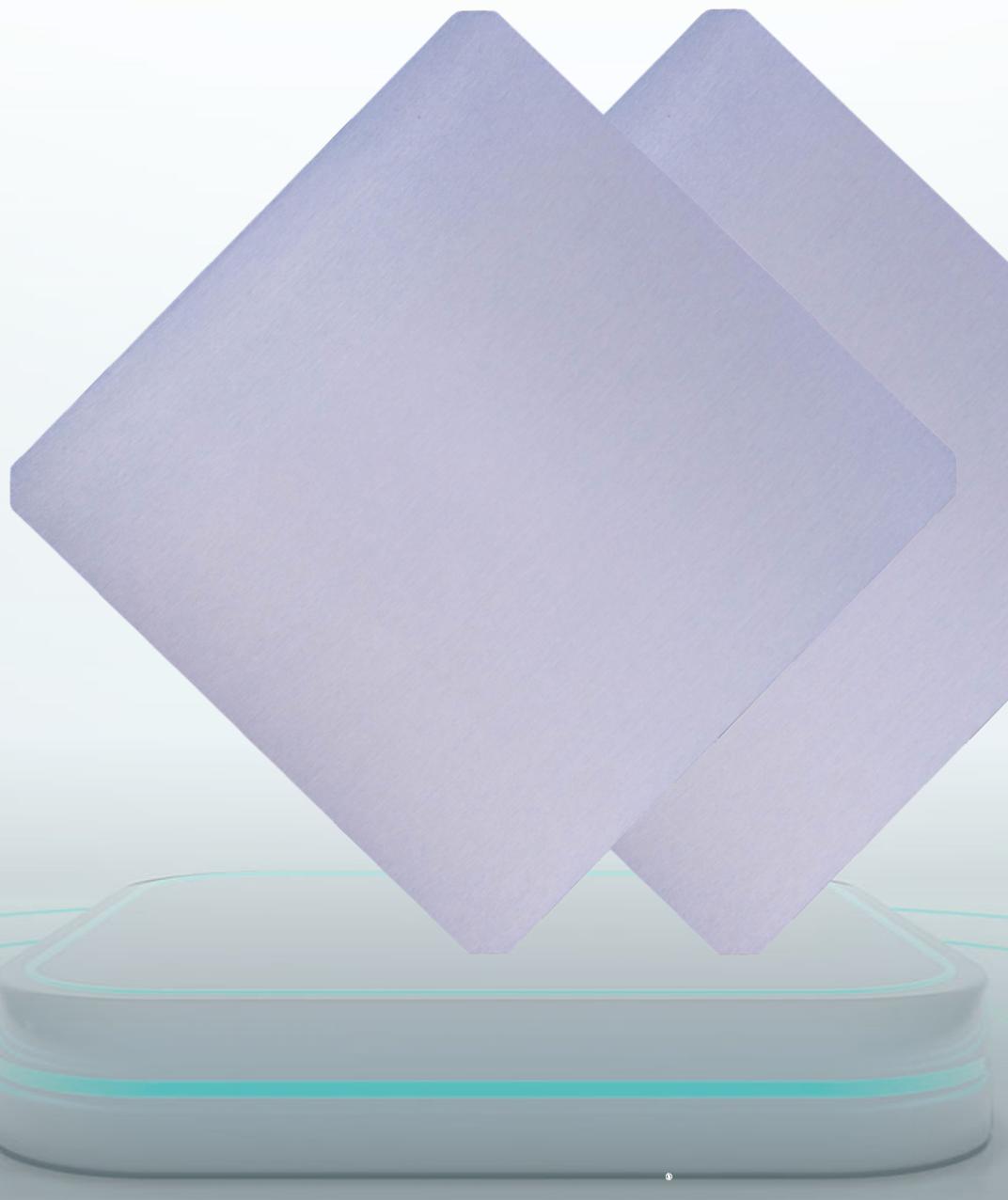
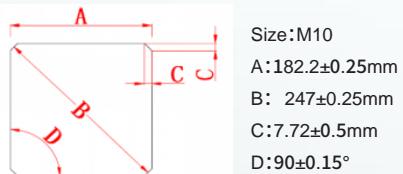
Comprehensive system certification

ISO 9001:2015

ISO 14001:2015

OHSAS 18001:2018

Schematic diagram of wafer size



Monocrystalline Wafer Specification

N-type M10

Key parameters

Conductivity type	N-type	P/N type tester(DLY-2 P/N)
Dopant	Phos.	--
Resistivity/Ω.cm	0.4-1.6	Wafer inspection system
MCLT(Minority carrier lifetime)/μs	≥1000	Transient with injection level:5E14cm ⁻³ (Sinton BCT-400)
Oxygen concentration [Oi]/at/cm ³	≤6.0×10 ¹⁷	FTIR(ASTM F121-83)
Carbon Concentration [Cs]/at/cm ³	≤5.0×10 ¹⁶	FTIR(GB/T 1558-2009)

Material properties

Growth method	CZ	--
Crystallinity	Monocrystalline	--
Etch pit density (dislocation density)/pcs/cm ²	≤500	Preferential Etch Techniques(ASTM F47-88)
Surface orientation/°	<100>±3	X-ray Diffraction Method (ASTM F26-1987)
Orientation of pseudo square sides/°	<010>, <001>±3	X-ray Diffraction Method (ASTM F26-1987)

Geometric dimensions and surface properties

Wafer model	M10	--
Geometry	Pseudo square	--
Bevel edge shape	Round	--
Wafer Side length/mm	182.2±0.25	Wafer inspection system
Wafer Diameter/mm	φ247±0.25	Wafer inspection system
Arc length projection/mm	7.72±0.5	Wafer inspection system
Angle between adjacent sides/°	90±0.15	Wafer inspection system
Thickness/μm	130±8	Wafer inspection system
Batch mean/μm	≥130	Wafer inspection system
Total thickness variation/μm	≤20	Wafer inspection system
Saw marks/μm	≤13	Wafer inspection system
Bow/μm	≤40	Wafer inspection system
Warp/μm	≤40	Wafer inspection system
Cutting method		--
Surface quality	as cut and cleaned, no visible contamination, color difference (as determined by standard sample) (oil or grease, finger prints, spot stains, epoxy/glue residue are not allowed)	Wafer inspection system
Chip	depth≤0.3mm & length≤0.5mm,Max 1/pcs, no V-chip	Naked eyes or wafer inspection system
Micro cracks / holes	Not allowed	Wafer inspection system



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Specifications subjects to technical changes and test , Jinghong Energy Technology Co., Ltd reserves the right of final interpretation

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